

RJK5013DPP

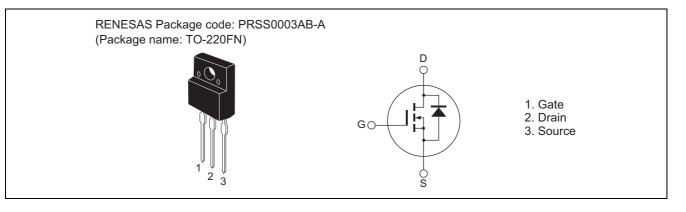
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1585-0100 Rev.1.00 Sep 28, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	$\frac{(1a-25 \text{ C})}{\text{Unit}}$
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D Note4	14	Α
Drain peak current	I _{D (pulse)} Note1	42	А
Body-drain diode reverse drain current	I _{DR}	14	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	42	А
Avalanche current	I _{AP} ^{Note3}	4	А
Avalanche energy	E _{AR} ^{Note3}	0.88	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

2. Value at Tc = $25^{\circ}C$

3. STch = 25°C, Tch \leq 150°C

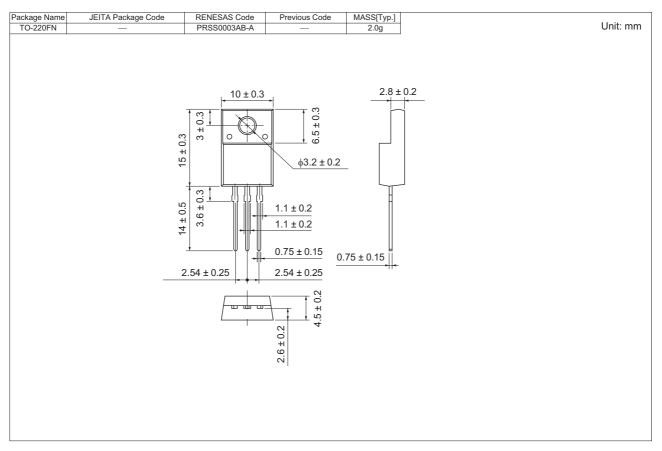
4. Limited by maximum safe operation area

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	500	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	—	—	1	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		—	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}		0.385	0.465	Ω	$I_D = 7 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss	_	1450	_	pF	$V_{DS} = 25 V$ $V_{GS} = 0$ f = 1 MHz
Output capacitance	Coss	_	155	—	pF	
Reverse transfer capacitance	Crss	_	19	—	pF	
Turn-on delay time	t _{d(on)}	_	34	—	ns	$I_D = 7 A$ $V_{GS} = 10 V$ $R_L = 35.7 \Omega$ $Rg = 10 \Omega$
Rise time	tr	_	24	—	ns	
Turn-off delay time	t _{d(off)}	—	86	—	ns	
Fall time	t _f	—	16	—	ns	
Total gate charge	Qg	—	38	—	nC	V _{DD} = 400 V
Gate to source charge	Qgs	—	8	—	nC	V _{GS} = 10 V I _D = 14 A
Gate to drain charge	Qgd	—	17	—	nC	
Body-drain diode forward voltage	V _{DF}	—	0.9	1.5	V	$I_F = 14 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}	_	310	—	ns	$I_F = 14 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 5. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
RJK5013DPP-00-T2	1050 pcs	Box (Tube)

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